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## September 2001

# FDS6375

# P-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

### **General Description**

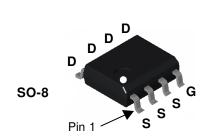
This PChannel 2.5V specified MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 8V).

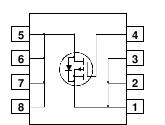
# Applications

- Power management
- Load switch
- Battery protection

# Features

- -8 A, -20 V.  $R_{DS(ON)} = 24 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$  $R_{DS(ON)} = 32 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
- Low gate charge (26 nC typical)
- + High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$
- High current and power handling capability





# Absolute Maximum Ratings T<sub>A=25°C</sub> unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
b	Drain Current – Continuous	(Note 1a)	-8	A
	- Pulsed		-50	
PD	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperation	ure Range	-55 to +175	°C
Therma	I Characteristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R <sub>0JA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1c)	125	°C/W
R <sub>0JC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

# **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6375	FDS6375	13"	12mm	2500 units

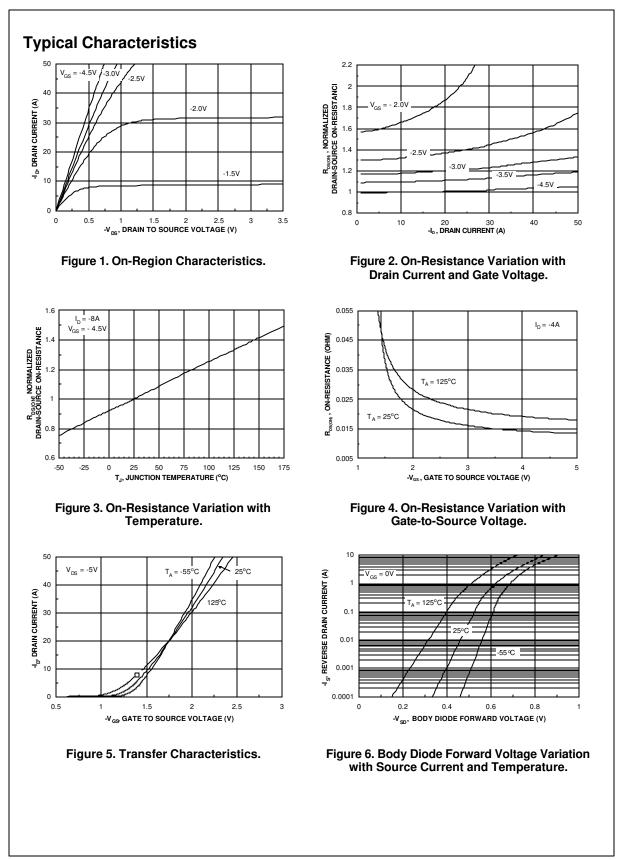
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FDS6375

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = -250 \mu A$	-20		[	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$ , Referenced to 25°C		-13		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -16 V$ , $V_{GS} = 0 V$			-1	μA
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 8 V$ , $V_{DS} = 0 V$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-0.4	-0.7	-1.5	V
$\Delta V_{GS(th)}$ $\Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to 25°C		3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source	$V_{GS} = -4.5 V, I_D = -8 A$		14	24	mΩ
	On-Resistance	$V_{GS} = -2.5 V$ , $I_D = -7 A$		19	32	
		$V_{GS} = -4.5 \text{ V}, \text{ I}_D = -8\text{A}, \text{ T}_J = 125^{\circ}\text{C}$		18	39	
D(on)	On–State Drain Current	$V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$	-50			A
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{\text{DS}} = -5 \text{ V}, \qquad I_{\text{D}} = -8 \text{ A}$		35		S
Dynamic	Characteristics		-		-	-
Ciss	Input Capacitance	$V_{DS} = -10 V$ , $V_{GS} = 0 V$ ,		2694		pF
Coss	Output Capacitance	f = 1.0 MHz		480		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			229		pF
Switchir	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD}=-10V, \qquad I_D=-1~A, \qquad$		12	22	ns
tr	Turn–On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \ \Omega$		9	17	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			124	197	ns
t <sub>f</sub>	Turn–Off Fall Time			57	92	ns
Qg	Total Gate Charge	$V_{DS} = -10 V$ , $I_D = -8 A$ ,		26	36	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 V$		5		nC
Q <sub>gd</sub>	Gate-Drain Charge			6		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings				
s	Maximum Continuous Drain-Source	Diode Forward Current			-2.1	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = -2.1 A$ (Note 2)		-0.7	-1.2	V
0001	of the junction-to-case and case-to-ambient thermal I R <sub>eJC</sub> is guaranteed by design while R <sub>eCA</sub> is determine a) 50 °C/W when mounted on a 1 iir				vhen mounte	

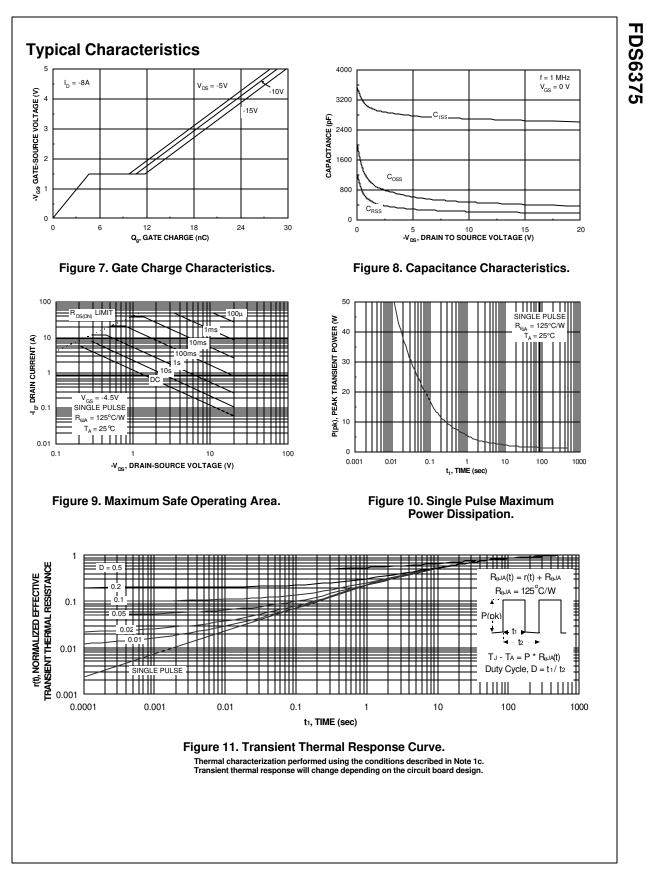
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%



FDS6375

FDS6375 Rev E(W)



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